Single 10-bit ADC; 65 Msps, 80 Msps, 105 Msps or 125 Msps; CMOS or LVDS DDR digital outputs

Rev. 2 — 28 December 2010

Product data sheet

1. General description

The ADC1010S is a single-channel 10-bit Analog-to-Digital Converter (ADC) optimized for high dynamic performance and low power consumption at sample rates up to 125 Msps. Pipelined architecture and output error correction ensure the ADC1010S is accurate enough to guarantee zero missing codes over the entire operating range. Supplied from a single 3 V source, it can handle output logic levels from 1.8 V to 3.3 V in CMOS mode, because of a separate digital output supply. It supports the Low Voltage Differential Signaling (LVDS) Double Data Rate (DDR) output standard. An integrated Serial Peripheral Interface (SPI) allows the user to easily configure the ADC. The device also includes a programmable full-scale SPI to allow a flexible input voltage range from 1 V to 2 V (peak-to-peak). With excellent dynamic performance from the baseband to input frequencies of 170 MHz or more, the ADC1010S is ideal for use in communications, imaging and medical applications.

2. Features and benefits

- SNR, 62 dBFS; SFDR, 86 dBc
- Sample rate up to 125 Msps
- 10-bit pipelined ADC core
- Clock input divided by 2 for less jitter
- Single 3 V supply
- Flexible input voltage range: 1 V (p-p) to 2 V (p-p)
- CMOS or LVDS DDR digital outputs
- Pin compatible with the ADC1410S series and the ADC1210S series

- Input bandwidth, 600 MHz
- Power dissipation, 430 mW at 80 Msps
- Serial Peripheral Interface (SPI)
- Duty cycle stabilizer
- Fast OuT-of-Range (OTR) detection
- Offset binary, two's complement, gray code
- Power-down and Sleep modes
- HVQFN40 package

3. Applications

- Wireless and wired broadband communications
- Spectral analysis
- Ultrasound equipment

- Portable instrumentation
- Imaging systems
- Software defined radio

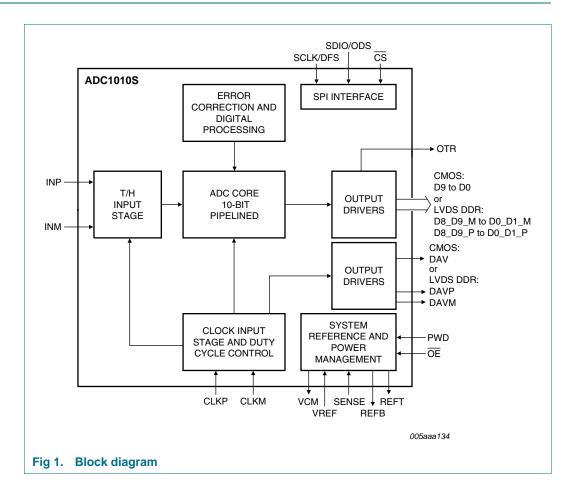


Single 10-bit ADC; CMOS or LVDS DDR digital outputs

4. Ordering information

Table 1. Ordering in	nformation										
Type number	f _s (Msps)	Package	Package								
		Name	Description	Version							
ADC1010S125HN/C1	125	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6 \times 6 \times 0.85$ mm	SOT618-1							
ADC1010S105HN/C1	105	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6 \times 6 \times 0.85$ mm	SOT618-1							
ADC1010S080HN/C1	80	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6 \times 6 \times 0.85$ mm	SOT618-1							
ADC1010S065HN/C1	65	HVQFN40	plastic thermal enhanced very thin quad flat package; no leads; 40 terminals; body $6 \times 6 \times 0.85$ mm	SOT618-1							

5. Block diagram

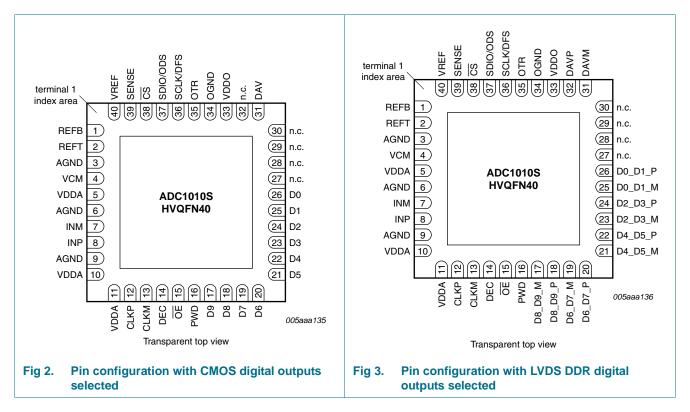


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Product data sheet

Single 10-bit ADC; CMOS or LVDS DDR digital outputs

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description (CMOS digital outputs)

			· · · ·
Symbol	Pin	Type <mark>[1]</mark>	Description
REFB	1	0	bottom reference
REFT	2	0	top reference
AGND	3	G	analog ground
VCM	4	0	common-mode output voltage
VDDA	5	Р	analog power supply
AGND	6	G	analog ground
INM	7	I	complementary analog input
INP	8	I	analog input
AGND	9	G	analog ground
VDDA	10	Р	analog power supply
VDDA	11	Р	analog power supply
CLKP	12	I	clock input
CLKM	13	I	complementary clock input
DEC	14	0	regulator decoupling node
OE	15	I	output enable, active LOW
PWD	16		power down, active HIGH

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Single 10-bit ADC; CMOS or LVDS DDR digital outputs

Table 2.	Pin desc	ription (CMC	DS digital outputs) continued
Symbol	Pin	Type <mark>[1]</mark>	Description
D9	17	0	data output bit 9 (Most Significant Bit (MSB))
D8	18	0	data output bit 8
D7	19	0	data output bit 7
D6	20	0	data output bit 6
D5	21	0	data output bit 5
D4	22	0	data output bit 4
D3	23	0	data output bit 3
D2	24	0	data output bit 2
D1	25	0	data output bit 1
D0	26	0	data output bit 0 (Least Significant Bit (LSB))
n.c.	27	-	not connected
n.c.	28	-	not connected
n.c.	29	-	not connected
n.c.	30	-	not connected
DAV	31	0	data valid output clock
n.c.	32	-	not connected
VDDO	33	Р	output power supply
OGND	34	G	output ground
OTR	35	0	out of range
SCLK/DFS	36	I	SPI clock
			data format select
SDIO/ODS	37	I/O	SPI data IO
			output data standard
CS	38	I	SPI chip select
SENSE	39	I	reference programming pin
VREF	40	I/O	voltage reference input/output

[1] P: power supply; G: ground; I: input; O: output; I/O: input/output.

Table 3. Pin description (LVDS DDR) digital outputs)

Symbol	Pin ^[1]	Type ^[2]	Description
D8_D9_M	17	0	differential output data D8 and D9 multiplexed, complement
D8_D9_P	18	0	differential output data D8 and D9 multiplexed, true
D6_D7_M	19	0	differential output data D6 and D7 multiplexed, complement
D6_D7_P	20	0	differential output data D6 and D7 multiplexed, true
D4_D5_M	21	0	differential output data D4 and D5 multiplexed, complement
D4_D5_P	22	0	differential output data D4 and D5 multiplexed, true
D2_D3_M	23	0	differential output data D2 and D3 multiplexed, complement
D2_D3_P	24	0	differential output data D2 and D3 multiplexed, true
D0_D1_M	25	0	differential output data D0 and D1 multiplexed, complement
D0_D1_P	26	0	differential output data D0 and D1 multiplexed, true
n.c.	27	-	not connected
n.c.	28	-	not connected
n.c.	29	-	not connected

Single 10-bit ADC; CMOS or LVDS DDR digital outputs

Pin description (LVDS DDR) digital outputs) ... continued Table 3.

Symbol	Pin ^[1]	Type ^[2]	Description
n.c.	30	-	not connected
DAVM	31	0	data valid output clock, complement
DAVP	32	0	data valid output clock, true

[1] Pins 1 to 16 and pins 33 to 40 are the same for both CMOS and LVDS DDR outputs (see Table 2).

[2] P: power supply; G: ground; I: input; O: output; I/O: input/output.

Limiting values 7.

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Vo	output voltage	pins D9 to D0 or pins D8_D9_P to D0_D1_P and D8_D9_M to D0_D1_M	-0.4	+3.9	V
V_{DDA}	analog supply voltage		-0.4	+3.9	V
V _{DDO}	output supply voltage		-0.4	+3.9	V
T _{stg}	storage temperature		-55	+125	°C
T _{amb}	ambient temperature		-40	+85	°C
Тj	junction temperature		-	125	°C

Thermal characteristics 8.

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		<mark>[1]</mark> 22.5	5 K/W
R _{th(j-c)}	thermal resistance from junction to case		[<u>1</u>] 11.7	K/W

[1] Value for six layers board in still air with a minimum of 25 thermal vias.

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Single 10-bit ADC; CMOS or LVDS DDR digital outputs

9. Static characteristics

$\begin{split} \textbf{Supplies} & \\ V_{\text{DDA}} & \text{analog supply voltage} & 2.85 & 3.0 & 3 \\ V_{\text{DDO}} & \text{output supply voltage} & CMOS mode & 1.65 & 1.8 & 3 \\ UVDS DDR mode & 2.85 & 3.0 & 3 \\ UVDS DDR mode & 2.85 & 3.0 & 3 \\ UVDS DDR mode & 2.85 & 3.0 & 3 \\ UVDS DDR mode & 2.85 & 3.0 & 3 \\ UDDA & \text{analog supply current} & CMOS mode; \ f_{at} = 70 MHz & -210 & $	ble 6.	Static characteristics ^[1]					
VDDA analog supply voltage 2.85 3.0 3.0 VDDO output supply voltage CMOS mode 1.65 1.8 3.0 3.0 IDDA analog supply current f _{elk} = 125 Msps; f _i = 70 MHz - 210 - IDDO output supply current f _i = 70 MHz - 10 - IDDO output supply current CMOS mode; f _{ak} = 125 Msps; f _i = 70 MHz - 35 - IDDO output supply current CMOS 1062; f _{ak} = 125 Msps; f _i = 70 MHz - 630 - P power dissipation ADC10105105; analog supply only - 550 - ADC101053065; analog supply only - 430 - - - ADC101053065; analog supply only - 800 - - - - - - COck inputs: pins CLKP and CLKM - - 20 - - - - - - - - - - - - - -	/mbol	Parameter	Conditions	Min	Тур	Max	Unit
Nome Output supply voltage CMOS mode 1.65 1.8 1.8 Nono analog supply current f _{alk} = 125 Msps; f ₁ = 70 MHz - 210 - Nono output supply current f _{alk} = 125 Msps; f ₁ = 70 MHz - 210 - Nono cMOS mode; f _{alk} = 125 Msps; f ₁ = 70 MHz - 10 - - 10 - LVDS DDR mode: f ₁ = 70 MHz - 10 - - 630 - P power dissipation ADC1010S125; analog supply only - 630 - ADC1010S080; analog supply only - - 550 - ADC1010S080; analog supply only - 430 - ADC1010S080; analog supply only - 430 - Sleep mode - 2 - - Cover-Voltage Positive Emitter-Coupled Logic (LVPECL) - 1.6 - Vitekoldt differential clock input voltage peak-to-peak - 1.6 - - -	upplies						
LVDS DDR mode2.853.03IDDAanalog supply current $f_{olk} = 125 Msps; f_i = 70 MHz-21010IDDOoutput supply currentCMOS mode; f_{ak} = 125 Msps; f_i = 70 MHz-1010LVDS DDR mode:f_{olk} = 125 Msps; f_i = 70 MHz-8301010Ppower dissipationADC10105125;analog supply only-83010ADC10105105;analog supply only-8301010ADC10105080;analog supply only-101010Clock inputs: pins CLKP and CLKMpeak-to-peak-1.61.6SINE wave-1.61.61.61.61.6Vite(old differential clock input voltagepeak-to-peak-1.61.6Logic inputs: pins PWD and OE1.61.61.6Logic inputs: pins PWD and OE1.61.61.6ViteLOW-level input voltage0-1.6$	DDA	analog supply voltage		2.85	3.0	3.4	V
$ \begin{tabular}{ c c c c } black $	DO	output supply voltage	CMOS mode	1.65	1.8	3.6	V
$\begin{tabular}{ c $			LVDS DDR mode	2.85	3.0	3.6	V
$\begin{tabular}{ c $	DA	analog supply current	f_{clk} = 125 Msps; f_i = 70 MHz	-	210	-	mA
fdik = 125 Msps; fi = 70 MHz ADC1010S125; analog supply only ADC1010S125; analog supply only ADC1010S105; analog supply only ADC1010S065; analog supply only ADC1010S1065; analog supply only ADC1010S105; ADC10E ADC1010S105; ADC10E ADC1010S105; ADC10E ADC1010S105; ADC10E ADC1010S105; ADC10E ADC1010S105; ADC10E ADC1010S10E ADC10E <	00	output supply current		-	10	-	mA
analog supply only ADC1010S105; analog supply only 550 ADC1010S060; analog supply only - 430 ADC1010S065; analog supply only - 430 ADC1010S065; analog supply only - 2 Power-down mode - 2 Sleep mode - 400 Clock inputs: pins CLKP and CLKM - 400 Clock inputs: pins clkP and CLKM - 1.6 Clock input voltage peak-to-peak - 1.6 SINE wave - 1.6 - Virakijdif differential clock input voltage peak - 1.6 Low Voltage Complementary Metal Oxide Semico-ductor (LVCMOS) - - - Low Voltage Input voltage 0.7VpDa - - - Vih HGH-level input voltage				-	35	-	mA
analog supply only - 430 ADC1010S080; analog supply only - 430 ADC1010S065; analog supply only - 880 Power-down mode - 2 Beep mode - 40 Steep mode - 40 Clock inputs: pins CLKP and CLKM - 40 Low-Voltage Positive Emitter-Coupled Logic (LVPECL) - 430 Vir(alk)dif differential clock input voltage peak-to-peak - 1.6 SINE wave - 1.6 - - - Vir(alk)dif differential clock input voltage peak-to-peak - 1.6 - SINE wave - 1.6 - - - - - Vir(alk)dif differential clock input voltage peak-to-peak - 1.6 -		power dissipation		-	630	-	mW
analog supply only ADC1010S065; analog supply only - 380 Power-down mode - 2 Sleep mode - 40 Clock inputs: pins CLKP and CLKM - 1.6 Low-Voltage Positive Emitter-Coupled Logic (LVPECL) - 1.6 Vi(clk/dif differential clock input voltage peak-to-peak - 1.6 SINE wave - ±3.0 - - - Vi(clk/dif differential clock input voltage peak - ±3.0 - Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS) - - - - Vi _{IL} LOW-level input voltage - - - - Logic inputs: pins PWD and OE - - - - - Vi _{IL} LOW-level input voltage 0 - - - - Vi _{IL} LOW-level input voltage 2 - - - - - - Vi _{IL} LOW-level input voltage 0 -<				-	550	-	mW
analog supply only Power-down mode - 2 Power-down mode - 40 - 40 - - 40 - - 40 - - - 40 - - - 40 -				-	430	-	mW
Sleep mode - 40 Clock inputs: pins CLKP and CLKM - 1.6 Low-Voltage Positive Emitter-Coupled Logic (LVPECL) - 1.6 Vi(clk)dif differential clock input voltage peak-to-peak - 1.6 SINE wave - ±3.0 -<				-	380	-	mW
Clock inputs: pins CLKP and CLKMLow-Voltage Positive Emitter-Coupled Logic (LVPECL)Vi(cik)difdifferential clock input voltagepeak-to-peak-1.6SINE waveVi(cik)difdifferential clock input voltagepeak-±3.0Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS)ViLLOW-level input voltageViHHIGH-level input voltage0.7V _{DDA} -Logic inputs: pins PWD and OE2ViLLOW-level input voltage0ViHHIGH-level input voltage2ViHHIGH-level input current-55-Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS0ViHHIGH-level input voltage0.7V _{DDA} ViLLOW-level input voltage0.7V _{DDA} Interface: pins CS, SDIO/ODS, SCLK/DFSViLLOW-level input voltage0.7V _{DDA} ViLLOW-level input voltage0.7V _{DDA} ViLLOW-level input voltage0.7V _{DDA} ViHHIGH-level input voltage0.7V _{DDA}			Power-down mode	-	2	-	mW
Low-Voltage Positive Emitter-Coupled Logic (LVPECL) Image: Stress of the s			Sleep mode	-	40	-	mW
Vi(clk)dif differential clock input voltage peak-to-peak - 1.6 SINE wave . <td>ock inpu</td> <td>uts: pins CLKP and CLKM</td> <td></td> <td></td> <td></td> <td></td> <td></td>	ock inpu	uts: pins CLKP and CLKM					
SiNE wave - ±3.0 Vi(clk)dif differential clock input voltage peak - ±3.0 Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS) -	w-Voltag	e Positive Emitter-Coupled Logic (LV	/PECL)				
Vi(clk)dif differential clock input voltage peak - ±3.0 Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS) - <th< td=""><td>(clk)dif</td><td>differential clock input voltage</td><td>peak-to-peak</td><td>-</td><td>1.6</td><td>-</td><td>V</td></th<>	(clk)dif	differential clock input voltage	peak-to-peak	-	1.6	-	V
Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS) VIL LOW-level input voltage -<	NE wave)					
VIL LOW-level input voltage - <td>(clk)dif</td> <td>differential clock input voltage</td> <td>peak</td> <td>-</td> <td>±3.0</td> <td>-</td> <td>V</td>	(clk)dif	differential clock input voltage	peak	-	±3.0	-	V
NIH HIGH-level input voltage 0.7V _{DDA} - Logic inputs: pins PWD and OE 0 - - VIL LOW-level input voltage 0 - - VIL LOW-level input voltage 2 -	w Voltag	e Complementary Metal Oxide Semi	conductor (LVCMOS)				
Logic inputs: pins PWD and OEVILLOW-level input voltage0-VIHHIGH-level input voltage2-IILLOW-level input current-55IIHHIGH-level input current-65Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS0-VILLOW-level input voltage0-VILLOW-level input voltage0.7V _{DDA} -VILHIGH-level input voltage0.7V _{DDA} -IILLOW-level input voltage0.7V _{DDA} -IILHIGH-level input current-10-	L	LOW-level input voltage		-	-	$0.3V_{DDA}$	V
V_{IL} LOW-level input voltage0- V_{IH} HIGH-level input voltage2- I_{IL} LOW-level input current-55 I_{IH} HIGH-level input current-65Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS V_{IL} LOW-level input voltage0- V_{IL} LOW-level input voltage0.7 V_{DDA} - V_{IL} LOW-level input voltage0.7 V_{DDA} - I_{IL} LOW-level input current-10- I_{IL} HIGH-level input current-50-	н	HIGH-level input voltage		$0.7V_{DDA}$	-	-	V
V_{IH} HIGH-level input voltage2-2 I_{IL} LOW-level input current-55- I_{IH} HIGH-level input current-65-Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS V_{IL} LOW-level input voltage0- V_{IH} HIGH-level input voltage0.7V _{DDA} - I_{IL} LOW-level input current-10- I_{IH} HIGH-level input current-50-	ogic inpu	its: pins PWD and OE					
I_{IL} LOW-level input current-55 I_{IH} HIGH-level input current-65Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS V_{IL} LOW-level input voltage0- V_{IL} LOW-level input voltage0.7V_{DDA}- V_{IL} LOW-level input voltage0.7V_DDA- I_{IL} LOW-level input current-10- I_{IH} HIGH-level input current-50-	L	LOW-level input voltage		0	-	0.8	V
IIH HIGH-level input current - 65 Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS 0 - 65 VIL LOW-level input voltage 0 - 65 VIH HIGH-level input voltage 0.7V _{DDA} - 65 IIL LOW-level input current -10 - - IIH HIGH-level input current -50 - -	Н	HIGH-level input voltage		2	-	V _{DDA}	V
Serial peripheral interface: pins CS, SDIO/ODS, SCLK/DFS V_{IL} LOW-level input voltage0- V_{IH} HIGH-level input voltage0.7V_{DDA}- I_{IL} LOW-level input current-10- I_{IH} HIGH-level input current-50-		LOW-level input current		-	55	-	μΑ
VILLOW-level input voltage0-VIHHIGH-level input voltage0.7V_DDA-IILLOW-level input current-10-IIHHIGH-level input current-50-		HIGH-level input current		-	65	-	μΑ
V_{IH} HIGH-level input voltage $0.7V_{DDA}$ -10 -10 -10 I_{IL} LOW-level input current -10 -50 -50	erial peri	pheral interface: pins CS, SDIO/OI	DS, SCLK/DFS				
ILLOW-level input current-10-IHHIGH-level input current-50-	L	LOW-level input voltage		0	-	$0.3V_{DDA}$	V
IILLOW-level input current-10-IIHHIGH-level input current-50-		HIGH-level input voltage		$0.7V_{DDA}$	-	V _{DDA}	V
I _{IH} HIGH-level input current -50 -		LOW-level input current		-10	-	+10	μΑ
		HIGH-level input current		-50	-	+50	μΑ
		input capacitance		-	4	-	pF

NXP Semiconductors

ADC1010S series

Single 10-bit ADC; CMOS or LVDS DDR digital outputs

HIGH-level output voltage 0.8V _{DOD} · V _{DOD} Co output capacitance high impedance; OE = HIGH - 3 - Output levels, V _{DDO} = 1.8 V V V 0.8V _{DDO} - 0.2V _C Vo _L LOW-level output voltage OGND - 0.2V _C Vo _H HIGH-level output voltage 0.8V _{DDO} - V _{DDO} Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9 M to D0_D1_M, DAVP and DAVM DAVP DAVP Output levels, V _{DDO} = 3 V only, R _L = 100 Ω - 1.2 - Vo(diffy differential output voltage output buffer current set to 3.5 mA - 1.2 - Vo(diffy differential noutput voltage output buffer current set to 3.5 mA -					c characteristics[1]continued	able 6. S
Output levels, $V_{DDO} = 3 V$ V_{OL} LOW-level output voltageOGND \circ $0.2V_{D}$ V_{OH} HIGH-level output voltage $0.8V_{DDO}$ \circ V_{DDO} C_{O} output capacitancehigh impedance; \overline{OE} = HIGH \circ 3 \circ Output levels, V_{DDO} = 1.8 V V_{OL} LOW-level output voltage $OGND$ \circ $0.2V_{D}$ V_{OL} LOW-level output voltage $0.8V_{DDO}$ V_{DDO} V_{DDO} V_{ODD} V_{ODD	Max L	Тур	Min	Conditions	Parameter	Symbol
VOLLOW-level output voltageOGND \sim $0.2V_{f}$ VOHHIGH-level output voltage $0.8V_{DDO}$ \sim V_{DDO} Cooutput capacitancehigh impedance; \overline{OE} = HIGH \sim 3 \sim Output levels, V_{DDO} = 1.8 V V_{OLO} $OGND$ \sim $0.2V_{f}$ VOLLOW-level output voltage $OGND$ \sim $0.2V_{f}$ Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9_M to D0_D1_M, DAVP and DAVMDOUtput levels, V_{DDO} = 3 V only, R_L = 100 Ω \sim Voltofitset)output offset voltageoutput buffer current set to 3.5 mA \sim 3.5 Voltofitset)differential output voltageoutput buffer current set to 3.5 mA \sim 1.2 Cooutput capacitance $ 3.6$ $-$ Nalog inputs: pins INP and INM $ 1.9.8$ $-$ Itinput current -5 $ 4.5$ R(dif)differential input resistance $ 1.2$ 2.5 Cit(ani)differential input voltagepeak-to-peak 1 1.5 2.5 Biinput bandwidth $ 650$ $ 1.5$ $-$ Vol(cm)common-mode output voltagepeak-to-peak 1 $ 2$ Common-mode output voltagepeak-to-peak 1 $ 2$ Common-mode output voltage $ 4$ $ 1$ $-$ Vol(cm)common-mode output voltage $ 4$ $ 1$ $-$ <				DTR, DAV	CMOS mode: pins D9 to D0, O	igital outpu
Oct HIGH-level output voltage 0.8 Vppo · Vopo Co output capacitance high impedance; OE = HIGH - 3 - Output levels, Vppo = 1.8 V V V 0.8 Vppo - 0.2 Vp Vol LOW-level output voltage 0.8 Vppo - 0.2 Vp Vol LOW-level output voltage 0.8 Vppo - 0.2 Vp Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9 M to D0_D1_M, DAVP and DAVM Output levels, Vppo = 3 V only, R_ = 100 Ω - 1.2 - Vo(diff) differential output voltage output buffer current set to 3.5 mA - - 1.2 - Vo(diff) differential nout resistance - 1.2 - - V(am) common-mode input voltage peak-to-peak 1 - 2.5 Ri(att) differential input resistance - 2.8 - - V(am) common-mode input voltage peak-to-peak 1 - 2.5 Bi input bandwidth - - </td <td></td> <td></td> <td></td> <td></td> <td>$D_{DO} = 3 V$</td> <td>Output levels</td>					$D_{DO} = 3 V$	Output levels
Co output capacitance high impedance; OE = HIGH - 3 - Output levels, V _{DDO} = 1.8 V V OGND - 0.2Vr VoL LOW-level output voltage OGND - 0.2Vr VoL LOW-level output voltage 0.8Vpoo - Vpoo Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9 M to D0_D1_M, DAVP and DAVM DAVM Output levels, Vpoo = 3 V only, RL = 100 Ω - 1.2 - Vo(offset) output offset voltage output buffer current set to 3.5 mA - 1.2 - Vo(dif) differential output voltage output buffer current set to 3.5 mA - - 45 Co output capacitance - 1.2 - - - Vo(dif) differential input resistance - 19.8 - - - - - - 2.5 G(qin) differential input capacitance - 1.1 1.5 2.5 - - - 2.5 - - 2.5 -	0.2V _{DDO} V	-	OGND		LOW-level output voltage	OL
Output levels, $V_{DDO} = 1.8 \text{ V}$ VOL LOW-level output voltage OGND \circ $0.2V_{DO}$ VOH HIGH-level output voltage 0.8 V_{DDO} \circ V_{DDO} Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9_M to D0_D1_M, DAVP and DAVM Output levels, $V_{DDO} = 3 \text{ V}$ only, $R_L = 100 \Omega$ \circ 1.2 \circ Vo(offiset) output offset voltage output buffer current set to 3.5 mA \circ 1.2 \circ Co output capacitance \circ 3.5 mA \circ 3.5 mA \circ Co output capacitance -5 \circ $+5$ \circ $+5$ Ri(dif) differential input resistance \circ 1.1 1.5 2.5 Bi input bandwidth \circ 2.8 \circ 2.5 2.5 Bi input bandwidth \circ 2.5 $2.$	V _{DDO} V	-	$0.8V_{DDO}$		HIGH-level output voltage	′он
VoL LOW-level output voltage OGND - 0.2 Vr VoDP VoH HIGH-level output voltage 0.8 VpDO - VpDO Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9_M to D0_D1_M, D4VP and D4VM D4VP D4VP D4VP Output levels, VpDO = 3 V only, RL = 100 Ω output offset voltage output buffer current set to 3.5 mA -	- р	3	-	high impedance; $\overline{OE} = HIGH$	output capacitance	ò
Nome HIGH-level output voltage 0.8Vppo · Vppo Digital outputs, LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9_M to D0_D1_M, DAVP and DAVM Output levels, Vppo = 3 V only, R_ = 100 Ω · 1.2 - Vo(offset) output offset voltage output buffer current set to 3.5 mA - 350 - Vo(off) differential output voltage output buffer current set to 3.5 mA - 350 - Vo(off) differential output voltage output buffer current set to 3.5 mA - 350 - Co output capacitance - 3 - <td></td> <td></td> <td></td> <td></td> <td>_{DDO} = 1.8 V</td> <td>Output levels</td>					_{DDO} = 1.8 V	Output levels
Digital outputs: LVDS mode: pins D8_D9_P to D0_D1_P, D8_D9_M to D0_D1_M, DAVP and DAVMOutput levels: $V_{DOO} = 3 V$ only, $R_L = 100 \Omega$ output buffer current set to 3.5 mA -1.2- $V_O(diff)$ differential output voltageoutput buffer current set to 3.5 mA -350- C_O output capacitance-3Analog inputs: pins INP and INM5-+5 $R_{i(dif)}$ differential input capacitance-1.2- $C_{i(dif)}$ differential input capacitance-19.8- $C_{i(dif)}$ differential input capacitance-2.8- $V_{I(cm)}$ common-mode input voltagepeak-to-peak11.52.5 B_i input bandwidth-650-2 $V_{O(cm)}$ common-mode output voltagepeak-to-peak1-2 $V_{O(cm)}$ common-mode output voltage- 4 $V_{O(cm)}$ common-mode output voltage-4 $V_{O(cm)}$ common-mode output voltage-4 $V_{O(cm)}$ common-mode output voltage-11 $V_{O(cm)}$ common-mode output voltagepoutput-4 $V_{O(cm)}$ common-mode output voltage-V_DA/2 $V_{O(cm)}$ common-mode output voltage4 $V_{O(cm)}$	0.2V _{DDO} V	-	OGND		LOW-level output voltage	OL
Output levels, $V_{DDO} = 3 V only, R_L = 100 \Omega$ $V_{O(offset)}$ output offset voltageoutput buffer current set to 3.5 mA -1.2- $V_{O(dif)}$ differential output voltageoutput buffer current set to 3.5 mA -350- C_O output capacitance-3Analog inputs: pins INP and INM5-+5 $R_{(dif)}$ differential input resistance-19.8- $C_{(idif)}$ differential input resistance-2.8- $C_{(idif)}$ differential input capacitance-650- $V_{(cm)}$ common-mode input voltagepeak-to-peak1-2 $V_{(cm)}$ common-mode output voltagepeak-to-peak1-2 $V_{O(cm)}$ common-mode output voltage-4 $V_{O(cm)}$ common-mode output voltage-4 $V_{O(cm)}$ common-mode output voltage-4 $V_{O(cm)}$ common-mode output current-4 $V_{O(cm)}$ common-mode output current-1-1 $V_{O(cm)}$ common-mode output current-4 $V_{O(cm)}$ common-mode output current-4 $V_{O(cm)}$ common-mode output current-1-1 $V_{O(cm)}$ common-mode output current1- <trr>$V_{O(cm)}$</trr>	V _{DDO} V	-	$0.8V_{DDO}$		HIGH-level output voltage	′он
$\begin{array}{cccccccccccccccccccccccccccccccccccc$		DAVM	DAVP and	D0_D1_P, D8_D9_M to D0_D1_M	LVDS mode: pins D8_D9_P to	igital outpu
Stream 3.5 mA Vo(dif) differential output voltage output buffer current set to 3.5 mA - 350 - Co output capacitance - 3 - Analog inputs: pins INP and INM - - 3 - It input current -5 - +5 Ri(dif) differential input resistance - 19.8 - C(diff) differential input capacitance - 2.8 - V(cm) common-mode input voltage VINP = VINM 1.1 1.5 2.5 Bi input bandwidth - 650 - - 2 V(cm) common-mode output voltage peak-to-peak 1 - 2 Common mode output voltage: pin VCM VDA/2 - - 4 - Vo(cm) common-mode output voltage peak-to-peak 1 - 2 - Vo(cm) common-mode output current - 4 - - - <td></td> <td></td> <td></td> <td></td> <td>$_{\text{DDO}}$ = 3 V only, R_L = 100 Ω</td> <td>Output levels</td>					$_{\text{DDO}}$ = 3 V only, R _L = 100 Ω	Output levels
Cooutput capacitance3.5 mACooutput capacitance-3-Analog inputs: pins INP and INM5<+5Itinput current-5<+5Ri(dif)differential input resistance-19.8-Ci(dif)differential input capacitance-2.8-V(cm)common-mode input voltageV_INP = V_INM1.11.52.5Biinput bandwidth-650V(dif)differential input voltagepeak-to-peak1-2Common mode output voltagepeak-to-peak1-2Vo(cm)common-mode output voltage-V_DDA / 2-Vo(cm)common-mode output voltage-4-Vo(cm)common-mode output voltage-0.5-1Vo(cm)common-mode output current-output0.5-1Voreference voltage: pin VREFoutput0.5-11VvREFvoltage on pin VREFoutputoutput0.5-1NLintegral non-linearity-±0.07-10.00DNLdifferential non-linearityguaranteed no missing codes-0.06±0.04±0.06Eoffsetoffset error-±2-10.52	- \	1.2	-	•	output offset voltage	O(offset)
Analog inputs: pins INP and INMI1input current-5-+5 $R_{i(dif)}$ differential input resistance-19.8- $C_{i(dif)}$ differential input capacitance-2.8- $V_{I(cm)}$ common-mode input voltage $V_{INP} = V_{INM}$ 1.11.52.5 B_i input bandwidth-650- $V_{I(dif)}$ differential input voltagepeak-to-peak1-2Common-mode output voltage-650- $V_{I(dif)}$ differential input voltagepeak-to-peak1-2Common-mode output voltagevoltage: pin VCMVolcm)-4-VO(cm)common-mode output current-4-I/O reference voltage: pin VREFVVREFvoltage on pin VREF0.05-1Input0.5-1AccuracyINLintegral non-linearity- ± 0.07 -DNLdifferential non-linearityguaranteed no missing codes-0.06 ± 0.04 ± 0.06 E_{offset} offset error- ± 2 - ± 2 -	- n	350	-	•	differential output voltage	O(dif)
$\begin{tabular}{ c c c c } $Input current & Input current & $	- р	3	-		output capacitance	ò
$\begin{array}{cccc} R_{i(dif)} & differential input resistance & - & 19.8 & - \\ C_{i(dif)} & differential input capacitance & - & 2.8 & - \\ V_{I(cm)} & common-mode input voltage & V_{INP} = V_{INM} & 1.1 & 1.5 & 2.5 \\ B_i & input bandwidth & - & 650 & - \\ V_{I(dif)} & differential input voltage & peak-to-peak & 1 & - & 2 \\ \hline V_{I(dif)} & differential input voltage & peak-to-peak & 1 & - & 2 \\ \hline V_{I(dif)} & common-mode output voltage & peak-to-peak & 1 & - & 2 \\ \hline V_{O(cm)} & common-mode output voltage & - & V_{DDA}/2 & - \\ I_{0(cm)} & common-mode output voltage & - & V_{DDA}/2 & - \\ \hline V_{O(cm)} & common-mode output current & - & 4 & - \\ \hline VO reference voltage: pin VREF & & & \\ \hline V_{VREF} & voltage on pin VREF & output & 0.5 & - & 1 \\ \hline nput & 0.5 & - & 1 \\ \hline nput & 0.5 & - & 1 \\ \hline Accuracy & & & \\ \hline NL & integral non-linearity & - & \pm 0.07 & - \\ DNL & differential non-linearity & guaranteed no missing codes & -0.06 & \pm 0.04 & +0.06 \\ \hline E_{offset} & offset error & & & & \\ \hline \end{array}$					pins INP and INM	nalog inpu
$ \begin{array}{c c c c c } & \mbox{differential input capacitance} & - & 2.8 & - \\ \hline C_{i(diff)} & \mbox{common-mode input voltage} & V_{INP} = V_{INM} & 1.1 & 1.5 & 2.5 \\ \hline B_i & \mbox{input bandwidth} & - & 650 & - \\ \hline V_{I(dif)} & \mbox{differential input voltage} & \mbox{peak-to-peak} & 1 & - & 2 \\ \hline Common mode output voltage: pin VCM & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output voltage} & - & V_{DDA} / 2 & - \\ \hline I_{0(cm)} & \mbox{common-mode output voltage} & - & 4 & - \\ \hline VO reference voltage: pin VREF & & & & \\ \hline V_{VREF} & \mbox{voltage on pin VREF} & \mbox{output} & 0.5 & - & 1 \\ \hline input & 0.5 & - & 1 \\ \hline input & 0.5 & - & 1 \\ \hline NL & \mbox{integral non-linearity} & & & & & \\ \hline NL & \mbox{differential non-linearity} & \mbox{guaranteed no missing codes} & -0.06 & \pm 0.04 & +0.06 \\ \hline E_{offset} & \mbox{offset error} & & & & & & \\ \hline \end{array}$	+ 5 μ	-	-5		nput current	
$ \begin{array}{cccc} V_{I(cm)} & \mbox{common-mode input voltage} & V_{INP} = V_{INM} & 1.1 & 1.5 & 2.5 \\ \hline B_i & \mbox{input bandwidth} & - & 650 & - \\ \hline V_{I(diff)} & \mbox{differential input voltage} & \mbox{peak-to-peak} & 1 & - & 2 \\ \hline Common wold = utput voltage: pin VCM & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output voltage} & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & & & & & & & & \\ \hline V_{O(cm)} & \mbox{common-mode output current} & & & & & & & & & & & & & & & & & & &$	- k	19.8	-		differential input resistance	Ri(dif)
$ \begin{array}{cccc} V_{ICCM} & \mbox{common-mode input voltage} & V_{INP} = V_{INM} & 1.1 & 1.5 & 2.5 \\ \hline B_i & \mbox{input bandwidth} & - & 650 & - \\ \hline V_{ICdiff} & \mbox{differential input voltage} & \mbox{peak-to-peak} & 1 & - & 2 \\ \hline Common wold = utput voltage: pin VCM & & & & & & & & \\ \hline V_{O(CM)} & \mbox{common-mode output voltage} & \mbox{peak-to-peak} & - & V_{DDA} / 2 & - \\ \hline I_{O(CM)} & \mbox{common-mode output voltage} & & & & & & & & & & \\ \hline V_{O(CM)} & \mbox{common-mode output current} & & & & & & & & & & & & \\ \hline I_{O(CM)} & \mbox{common-mode output current} & & & & & & & & & & & & & & & \\ \hline I_{O(CM)} & \mbox{common-mode output current} & & & & & & & & & & & & & & & & & & &$	- р	2.8	-		differential input capacitance	i(dif)
$\begin{array}{ccccccc} B_{i} & \mbox{input bandwidth} & \mbox{input bandwidth} & \mbox{input voltage} & \mbox{peak-to-peak} & 1 & \mbox{orm} & 1 & \mbox{orm} & 2 & \mbox{common mode output voltage: pin VCM} & \mbox{input voltage: pin VCM} & \mbox{input output voltage} & \mbox{ormmon-mode output voltage} & \mbox{ormmon-mode output voltage} & \mbox{ormmon-mode output current} & \mbox{ormmon-mode output current} & \mbox{input output current} & \mbox{ormmon-mode output current} & \mbox{input output output current} & \mbox{input output current} & \mbox{input output output current} & input output out$	2.5 V	1.5	1.1	$V_{INP} = V_{INM}$	common-mode input voltage	
	- N	650	-		nput bandwidth	
$\begin{array}{c c c c c c } \hline V_{O(cm)} & common-mode output voltage & - & V_{DDA}/2 & - & & & & & & & & & & & & & & & & & $	2 V	-	1	peak-to-peak	differential input voltage	/I(dif)
$\begin{array}{c c c c c c c c c c c c c c c c c c c $					output voltage: pin VCM	common mo
I/O reference voltage: pin VREF V_{VREF} voltage on pin VREFoutput0.5-1input0.5-1AccuracyINLintegral non-linearity- ± 0.07 -DNLdifferential non-linearityguaranteed no missing codes-0.06 ± 0.04 ± 0.06 E_{offset} offset error- ± 2 -	- V	V _{DDA} / 2	-		common-mode output voltage	O(cm)
V_{VREF} voltage on pin VREFoutput input0.5-1AccuracyINLintegral non-linearity ± 0.07 -DNLdifferential non-linearityguaranteed no missing codes-0.06 ± 0.04 ± 0.06 E_{offset} offset error- ± 2 -	- n	4	-		common-mode output current	D(cm)
input 0.5 -1AccuracyINLintegral non-linearity- ± 0.07 -DNLdifferential non-linearityguaranteed no missing codes -0.06 ± 0.04 ± 0.06 E_{offset} offset error- ± 2 -					ltage: pin VREF	O reference
Accuracy - ±0.07 - INL integral non-linearity guaranteed no missing codes -0.06 ±0.04 +0.06 DNL differential non-linearity guaranteed no missing codes -0.06 ±0.04 +0.06 E _{offset} offset error - ±2 -	1 V	-	0.5	output	voltage on pin VREF	VREF
INLintegral non-linearity- ± 0.07 -DNLdifferential non-linearityguaranteed no missing codes -0.06 ± 0.04 ± 0.06 E_{offset} offset error- ± 2 -	1 V	-	0.5	input		
DNLdifferential non-linearityguaranteed no missing codes -0.06 ± 0.04 $+0.06$ E_{offset} offset error- ± 2 -						ccuracy
E _{offset} offset error - ±2 -	- L	±0.07	-		ntegral non-linearity	NL
	+0.06 L	±0.04	-0.06	guaranteed no missing codes	differential non-linearity	NL
	- n	±2	-		offset error	offset
	9	±0.5		full-scale	gain error	G
Supply						upply
PSRR power supply rejection ratio 200 mV (p-p) on V_{DDA} ; $f_i = DC54 -$	- d	-54	-	200 mV (p-p) on V_{DDA} ; f _i = DC	power supply rejection ratio	SRR

[1] Typical values measured at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$, $T_{amb} = 25 \text{ °C}$ and $C_L = 5 \text{ pF}$; minimum and maximum values are across the full temperature range $T_{amb} = -40 \text{ °C}$ to +85 °C at $V_{DDA} = 3 \text{ V}$, $V_{DDO} = 1.8 \text{ V}$; $V_{INP} - V_{INM} = -1 \text{ dBFS}$; internal reference mode; applied to CMOS and LVDS interface; unless otherwise specified.

10. Dynamic characteristics

10.1 Dynamic characteristics

Dynamic characteristics^[1] Table 7.

Symbol	Parameter	Conditions	ADC1010S065 ADC1010S080						AD	C1010S	105	ADC1010S125			
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Analog s	ignal processin	g													
α_{2H}	second	f _i = 3 MHz	-	87	-	-	87	-	-	89	-	-	91	-	dBc
	harmonic level	f _i = 30 MHz	-	86	-	-	86	-	-	89	-	-	90	-	dBo
		$f_i = 70 \text{ MHz}$	-	85	-	-	85	-	-	87	-	-	88	-	dBo
		$f_i = 170 \text{ MHz}$	-	82	-	-	82	-	-	84	-	-	86	-	dBo
α _{3H}	third harmonic	$f_i = 3 MHz$	-	86	-	-	86	-	-	88	-	-	90	-	dBo
	level	$f_i = 30 \text{ MHz}$	-	85	-	-	85	-	-	88	-	-	89	-	dBo
		$f_i = 70 \text{ MHz}$	-	84	-	-	84	-	-	86	-	-	87	-	dBo
		$f_i = 170 \text{ MHz}$	-	81	-	-	81	-	-	83	-	-	85	-	dBo
THD	total harmonic	$f_i = 3 MHz$	-	83	-	-	83	-	-	85	-	-	87	-	dBo
	distortion	$f_i = 30 \text{ MHz}$	-	82	-	-	82	-	-	85	-	-	86	-	dBo
		$f_i = 70 \text{ MHz}$	-	81	-	-	81	-	-	83	-	-	84	-	dBo
		f _i = 170 MHz	-	78	-	-	78	-	-	80	-	-	82	-	dBo
ENOB	effective	$f_i = 3 MHz$	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
	number of bits	$f_i = 30 \text{ MHz}$	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
		$f_i = 70 \text{ MHz}$	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
		f _i = 170 MHz	-	9.9	-	-	9.9	-	-	9.9	-	-	9.9	-	bits
SNR	signal-to-noise	$f_i = 3 MHz$	-	61.7	-	-	61.7	-	-	61.6	-	-	61.6	-	dBF
	ratio	$f_i = 30 \text{ MHz}$	-	61.6	-	-	61.6	-	-	61.6	-	-	61.6	-	dBF
		$f_i = 70 \text{ MHz}$	-	61.6	-	-	61.6	-	-	61.5	-	-	61.5	-	dBF
		f _i = 170 MHz	-	61.5	-	-	61.5	-	-	61.5	-	-	61.5	-	dBF
SFDR	spurious-free	$f_i = 3 \text{ MHz}$	-	86	-	-	86	-	-	88	-	-	90	-	dBo
	dynamic range	$f_i = 30 \text{ MHz}$	-	85	-	-	85	-	-	88	-	-	89	-	dBo
		$f_i = 70 \text{ MHz}$	-	84	-	-	84	-	-	86	-	-	87	-	dBo
		f _i = 170 MHz	-	81	-	-	81	-	-	83	-	-	85	-	dBo

NXP Semiconductors

Single 10-bit ADC; CMOS or LVDS DDR digital outputs ADC1010S series

Single 10-bit ADC; CMOS or LVDS DDR digital outputs

ADC1010S

series

Table 7. Dynamic characteristics^[1] ...continued

1010S	Symbol	Parameter	Conditions	AD	C1010S	065	AD	C1010S	080	AD	C1010S [,]	05	ADC	C1010S1	25	Unit
SER			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max		
	IMD	Intermodulation	$f_i = 3 \text{ MHz}$	-	89	-	-	89	-	-	92	-	-	93	-	dBc
	distortion	$f_i = 30 \text{ MHz}$	-	88	-	-	88	-	-	92	-	-	92	-	dBc	
		$f_i = 70 \text{ MHz}$	-	87	-	-	87	-	-	90	-	-	90	-	dBc	
			f _i = 170 MHz	-	84	-	-	85	-	-	87	-	-	88	-	dBc

[1] Typical values measured at V_{DDA} = 3 V, V_{DDO} = 1.8 V, T_{amb} = 25 °C and C_L = 5 pF; minimum and maximum values are across the full temperature range T_{amb} = -40 °C to +85 °C at V_{DDA} = 3 V, V_{DDO} = 1.8 V; V_{INP} - V_{INM} = -1 dBFS; internal reference mode; applied to CMOS and LVDS interface; unless otherwise specified.

10.2 Clock and digital output timing

Table 8. Clock input and digital output timing characteristics^[1]

Symbol	Parameter	Conditions	AD	C1010S	065	AD	C1010S	080	AD	C1010S	105	ADC1010S125			Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Clock tim	ing input: pins	CLKP and CLKM													
f _{clk}	clock frequency		40	-	65	60	-	80	75	-	105	100	-	125	MHz
t _{lat(data)}	data latency time		-	13.5	-	-	13.5	-	-	13.5	-	-	13.5	-	clock cycles
δ_{clk}	clock duty	DCS_EN = logic 1	30	50	70	30	50	70	30	50	70	30	50	70	%
	cycle	DCS_EN = logic 0	45	50	55	45	50	55	45	50	55	45	50	55	%
t _{d(s)}	sampling delay time		-	0.8	-	-	0.8	-	-	0.8	-	-	0.8	-	ns
t _{wake}	wake-up time		-	76	-	-	76	-	-	76	-	-	76	-	μS
CMOS Mo	ode timing outp	out: pins D9 to D0 and D	AV												
t _{PD}	propagation	DATA	13.6	14.9	16.4	11.9	12.9	14.4	8.0	10.8	12.4	8.2	9.7	11.3	ns
	delay	DAV	-	4.2	-	-	3.6	-	-	3.3	-	-	3.4	-	ns
t _{su}	set-up time		-	12.5	-	-	9.8	-	-	6.8	-	-	5.6	-	ns
t _h	hold time		-	3.4	-	-	3.3	-	-	3.1	-	-	2.8	-	ns
t _r	rise time	DATA	0.39	-	2.4	0.39	-	2.4	0.39	-	2.4	0.39	-	2.4	ns
		DAV	0.26	-	2.4	0.26	-	2.4	0.26	-	2.4	0.26	-	2.4	ns
t _f	fall time	DATA	0.19	-	2.4	0.19	-	2.4	0.19	-	2.4	0.19	-	2.4	ns

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Product data sheet

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	Table 8.	Clock input and digital output timing characteristics[1] continued	
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Table 8.	Clock input a	nd digital output timing ch	naracter	istics ^[1]	continu	ed									
Symbol	Parameter	Conditions	AD	C1010S	065	AD	C1010S	080	AD	C1010S	105	ADO	C1010S [,]	125	Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
LVDS DD	R mode timing	output: pins D8_D9_P to I	D0_D1_I	P, D8_D9	_M to D	0_D1_N	I, DAVP	and DA	VM						
t _{PD}	propagation	DATA	3.3	5.1	7.6	2.9	4.6	7.1	2.5	4.2	6.8	2.2	4.0	6.6	ns
	delay	DAV	-	2.8	-	-	2.5	-	-	2.3	-	-	2.2	-	ns
t _{su}	set-up time		-	5.4	-	-	4.1	-	-	2.6	-	-	1.9	-	ns
t _h	hold time		-	2.2	-	-	2.0	-	-	1.8	-	-	1.7	-	ns
t _r	rise time	DATA [3]	0.5	-	5	0.5	-	5	0.5	-	5	0.5	-	5	ns
		DAV	0.18	-	2.4	0.18	-	2.4	0.18	-	2.4	0.18	-	2.4	ns
t _f	fall time	DATA [3]	0.15	-	1.6	0.15	-	1.6	0.15	-	1.6	0.15	-	1.6	ns

[1] Typical values measured at $V_{DDA} = 3 V$, $V_{DDO} = 1.8 V$, $T_{amb} = 25 °C$ and $C_L = 5 pF$; minimum and maximum values are across the full temperature range $T_{amb} = -40 °C$ to +85 °C at $V_{DDA} = 3 V$, $V_{DDO} = 1.8 V$; $V_{INP} - V_{INM} = -1 dBFS$; internal reference mode; applied to CMOS and LVDS interface; unless otherwise specified.

[2] Measured between 20 % to 80 % of V_{DDO}.

Rise time measured from -50 mV to +50 mV; fall time measured from +50 mV to -50 mV. [3]

All inf

Single 10-bit ADC; CMOS or LVDS DDR digital outputs

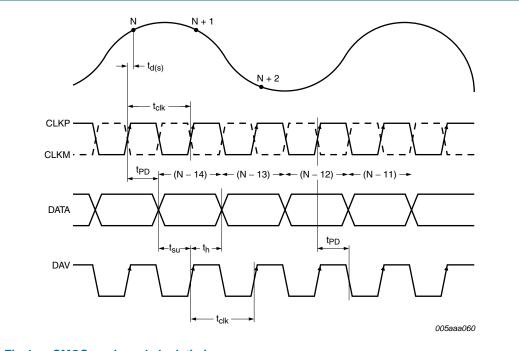
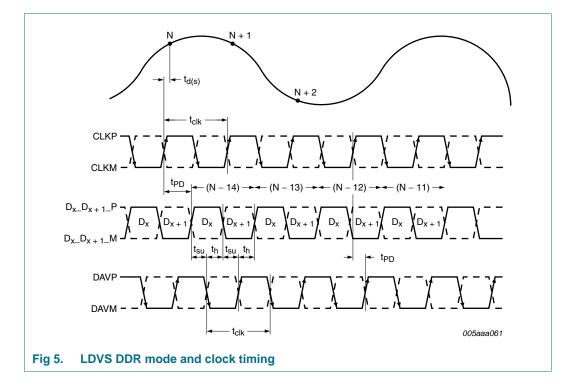


Fig 4. CMOS mode and clock timing



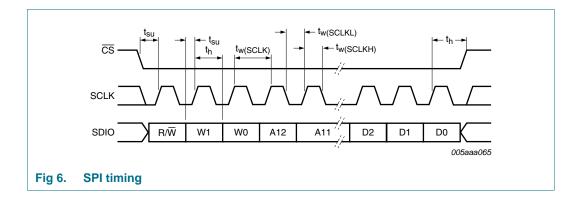
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10.3 SPI timings

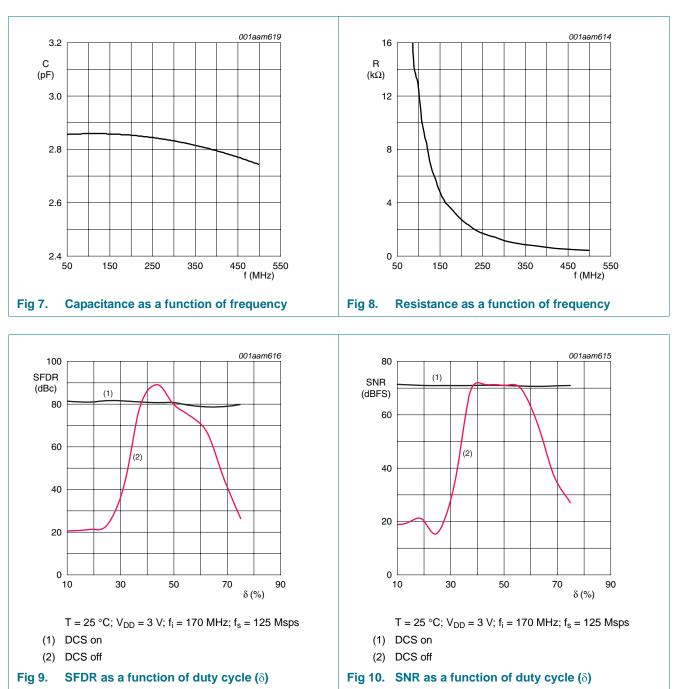
Table 9.	SPI timings characteristics ^[1]					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{w(SCLK)}	SCLK pulse width		-	40	-	ns
t _{w(SCLKH)}	SCLK HIGH pulse width		-	16	-	ns
t _{w(SCLKL)}	SCLK LOW pulse width		-	16	-	ns
t _{su}	set-up time	data to SCLK HIGH	-	5	-	ns
		CS to SCLK HIGH	-	5	-	ns
t _h	hold time	data to SCLK HIGH	-	2	-	ns
		CS to SCLK HIGH	-	2	-	ns
f _{clk(max)}	maximum clock frequency		-	25	-	MHz

[1] Typical values measured at V_{DDA} = 3 V, V_{DDO} = 1.8 V, T_{amb} = 25 °C and C_L = 5 pF; minimum and maximum values are across the full temperature range T_{amb} = -40 °C to +85 °C at V_{DDA} = 3 V, V_{DDO} = 1.8 V



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10.4 Typical characteristics

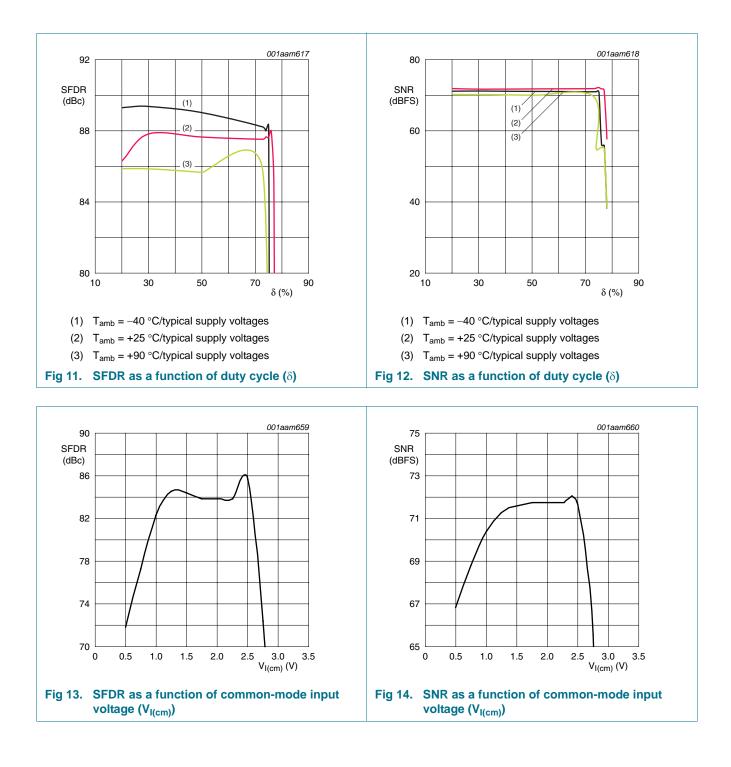
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11. Application information

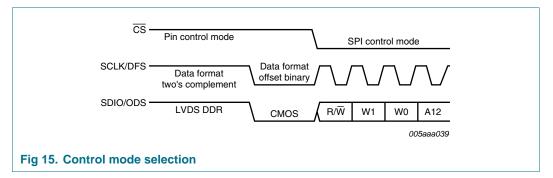
11.1 Device control

The ADC1010S can be controlled via SPI or directly via the I/O pins (Pin control mode).

11.1.1 SPI and Pin control modes

The device enters Pin control mode at power-up, and remains in this mode as long as pin \overline{CS} is held HIGH. In Pin control mode, the SPI pins SDIO, \overline{CS} and SCLK are used as static control pins.

SPI control mode is enabled by forcing pin \overline{CS} LOW. Once SPI control mode has been enabled, the device remains in this mode. The transition from Pin control mode to SPI control mode is illustrated in Figure 15.



When the device enters SPI control mode, the output data standard and data format are determined by the level on pin SDIO at the instant a transition is triggered by a falling edge on CS.

11.1.2 Operating mode selection

The active ADC1010S operating mode (Power-up, Power-down or Sleep) can be selected via the SPI interface (see <u>Table 20</u>) or by using pins PWD and OE in Pin control mode, as described in <u>Table 10</u>.

Pin PWD	Pin OE	Operating mode	Output high-Z
LOW	LOW	Power-up	no
LOW	HIGH	Power-up	yes
HIGH	LOW	Sleep	yes
HIGH	HIGH	Power-down	yes

Table 10. Operating mode selection via pin PWD and OE

11.1.3 Selecting the output data standard

The output data standard (CMOS or LVDS DDR) can be selected via the SPI interface (see <u>Table 23</u>) or by using pin ODS in Pin control mode. LVDS DDR is selected when ODS is HIGH, otherwise CMOS is selected.

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11.1.4 Selecting the output data format

The output data format can be selected via the SPI interface (offset binary, two's complement or gray code; see <u>Table 23</u>) or by using pin DFS in Pin control mode (offset binary or two's complement). Offset binary is selected when DFS is LOW. When DFS is HIGH, two's complement is selected.

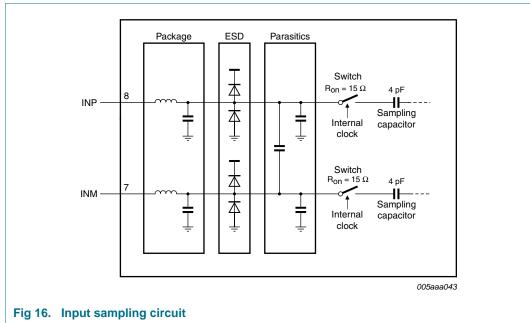
11.2 Analog inputs

11.2.1 Input stage

The analog input of the ADC1010S supports a differential or a single-ended input drive. Optimal performance is achieved using differential inputs with the common-mode input voltage ($V_{l(cm)}$) on pins INP and INM set to 0.5 V_{DDA} .

The full-scale analog input voltage range is configurable between 1 V (p-p) and 2 V (p-p) via a programmable internal reference (see <u>Section 11.3</u> and <u>Table 22</u>).

The equivalent circuit of the sample and hold input stage, including Electrostatic Discharge (ESD) protection and circuit and package parasitics, is shown in Figure 16.



The sample phase occurs when the internal clock (derived from the clock signal on pin CLKP/CLKM) is HIGH. The voltage is then held on the sampling capacitors. When the clock signal goes LOW, the stage enters the hold phase and the voltage information is

11.2.2 Anti-kickback circuitry

transmitted to the ADC core.

Anti-kickback circuitry (R-C filter in Figure 17) is needed to counteract the effects of a charge injection generated by the sampling capacitance.

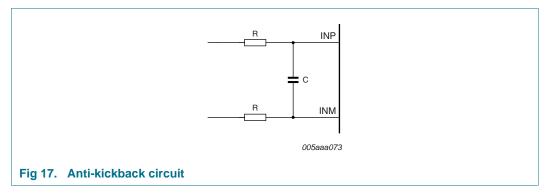
The RC filter is also used to filter noise from the signal before it reaches the sampling stage. The value of the capacitor should be chosen to maximize noise attenuation without degrading the settling time excessively.

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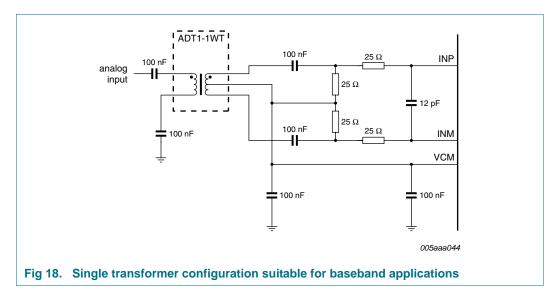
The component values are determined by the input frequency and should be selected so as not to affect the input bandwidth.

Table 11.	RC coupling versus input frequency - typical values
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Input frequency	R	C
3 MHz	25 Ω	12 pF
70 MHz	12 Ω	8 pF
170 MHz	12 Ω	8 pF

11.2.3 Transformer

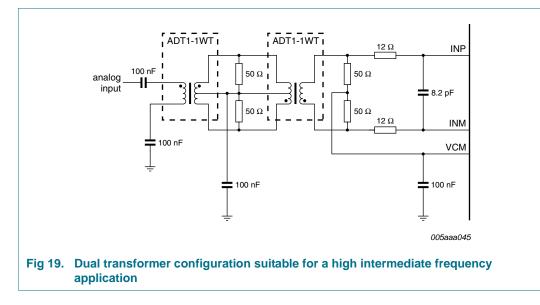
The configuration of the transformer circuit is determined by the input frequency. The configuration shown in Figure 18 would be suitable for a baseband application.



The configuration shown in Figure 19 is recommended for high frequency applications. In both cases, the choice of transformer is a compromise between cost and performance.

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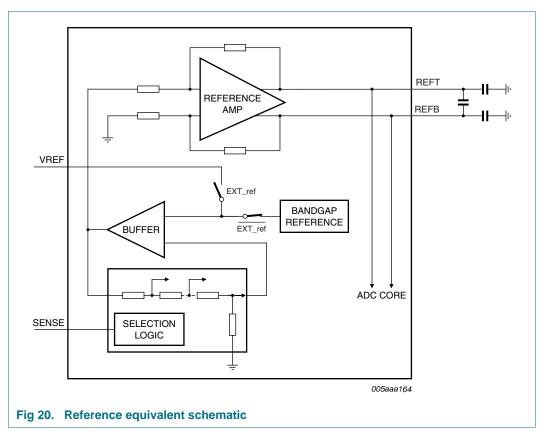


11.3 System reference and power management

11.3.1 Internal/external references

The ADC1010S has a stable and accurate built-in internal reference voltage to adjust the ADC full-scale. This reference voltage can be set internally via SPI or with pins VREF and SENSE (programmable in 1 dB steps between 0 dB and –6 dB via control bits INTREF[2:0] when bit INTREF_EN = logic 1; see <u>Table 22</u>). See <u>Figure 21</u> to <u>Figure 24</u>. The equivalent reference circuit is shown in <u>Figure 20</u>. An external reference is also possible by providing a voltage on pin VREF as described in <u>Figure 23</u>.

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If bit INTREF_EN is set to logic 0, the reference voltage is determined either internally or externally as detailed in Table 12.

Table 12. Reference selection

Selection	SPI bit INTREF_EN	SENSE pin	VREF pin	Full-scale (p-p)
internal (<u>Figure 21</u>)	0	AGND	330 pF capacitor to AGND	2 V
internal (<u>Figure 22</u>)	0	pin VREF conn a 330 pF capac	ected to pin SENSE and via citor to AGND	1 V
external (<u>Figure 23</u>)	0	V _{DDA}	external voltage between 0.5 V and 1 V ^[1]	1 V to 2 V
internal via SPI (Figure 24)	1	pin VREF conn 330 pF capacite	ected to pin SENSE and via or to AGND	1 V to 2 V

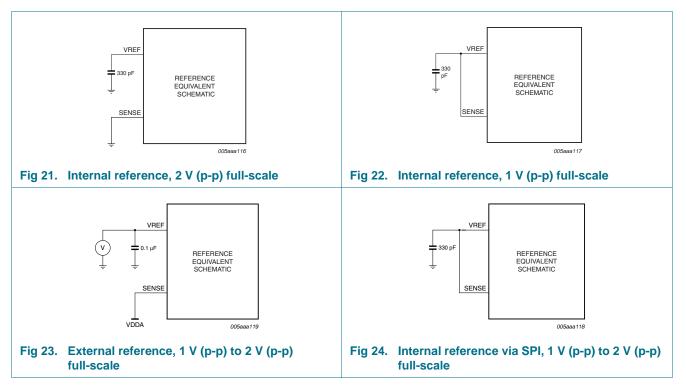
[1] The voltage on pin VREF is doubled internally to generate the internal reference voltage.

Figure 21 to Figure 24 illustrate how to connect the SENSE and VREF pins to select the required reference voltage source.

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11.3.2 Programmable full-scale

The full-scale is programmable between 1 V (peak-to-peak) to 2 V (peak-to-peak) (see <u>Table 13</u>).

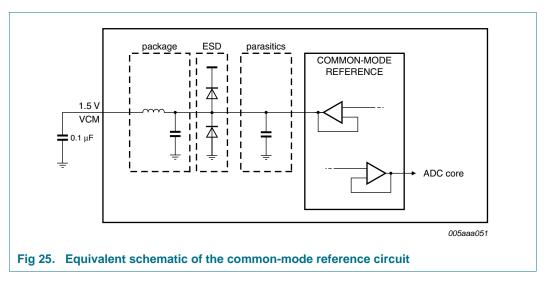
Table 13. Reference of I gain control				
INTREF[2:0]	Gain (dB)	Full-scale (V (p-p))		
000	0	2		
001	-1	1.78		
010	-2	1.59		
011	-3	1.42		
100	-4	1.26		
101	-5	1.12		
110	-6	1		
111	reserved	х		

Table 13. Reference SPI gain control

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11.3.3 Common-mode output voltage (V_{O(cm)})

A 0.1 μ F filter capacitor should be connected between pin VCM and ground to ensure a low-noise common-mode output voltage. When AC-coupled, pin VCM can then be used to set the common-mode reference for the analog inputs, for instance via a transformer middle point.



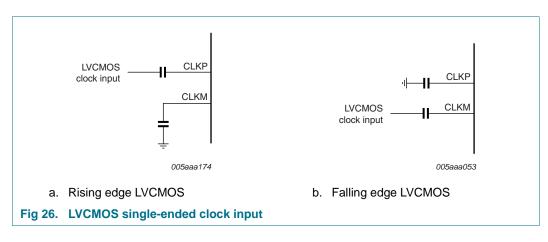
11.3.4 Biasing

The common-mode input voltage ($V_{I(cm)}$) on pins INP and INM should be set externally to 0.5 V_{DDA} for optimal performance and should always be between 0.9 V and 2 V.

11.4 Clock input

11.4.1 Drive modes

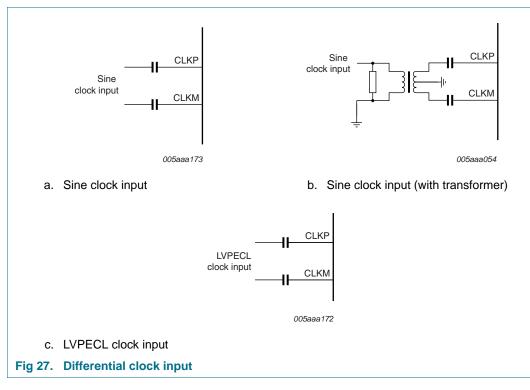
The ADC1010S can be driven differentially (LVPECL). It can also be driven by a single-ended Low Voltage Complementary Metal Oxide Semiconductor (LVCMOS) signal connected to pin CLKP (pin CLKM should be connected to ground via a capacitor) or pin CLKM (pin CLKP should be connected to ground via a capacitor).



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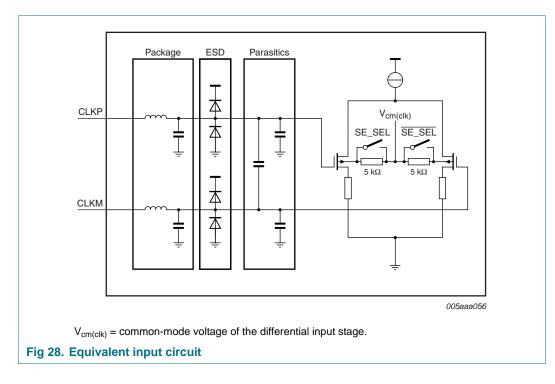
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11.4.2 Equivalent input circuit

The equivalent circuit of the input clock buffer is shown in Figure 28. The common-mode voltage of the differential input stage is set via internal 5 k Ω resistors.



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Single-ended or differential clock inputs can be selected via the SPI interface (see <u>Table 21</u>). If single-ended is enabled, the input pin (CLKM or CLKP) is selected via control bit SE_SEL.

If single-ended is implemented without setting bit SE_SEL to the appropriate value, the unused pin should be connected to ground via a capacitor.

11.4.3 Duty cycle stabilizer

The duty cycle stabilizer can improve the overall performance of the ADC by compensating the duty cycle of the input clock signal. When the duty cycle stabilizer is active (bit DCS_EN = logic 1; see Table 21), the circuit can handle signals with duty cycles of between 30 % and 70 % (typical). When the duty cycle stabilizer is disabled (DCS_EN = logic 0), the input clock signal should have a duty cycle of between 45 % and 55 %.

11.4.4 Clock input divider

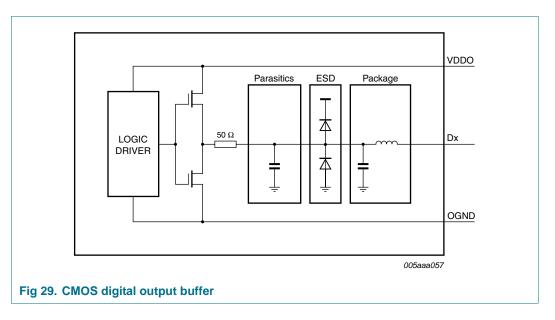
The ADC1010S contains an input clock divider that divides the incoming clock by a factor of 2 (when bit CLKDIV = logic 1; see <u>Table 21</u>). This feature allows the user to deliver a higher clock frequency with better jitter performance, leading to a better SNR result once acquisition has been performed.

11.5 Digital outputs

11.5.1 Digital output buffers: CMOS mode

The digital output buffers can be configured as CMOS by setting bit LVDS_CMOS to logic 0 (see Table 23).

Each digital output has a dedicated output buffer. The equivalent circuit of the CMOS digital output buffer is shown in Figure 29. The buffer is powered by a separate power supply, pins OGND and VDDO, to ensure 1.8 V to 3.3 V compatibility and is isolated from the ADC core. Each buffer can be loaded by a maximum of 10 pF.

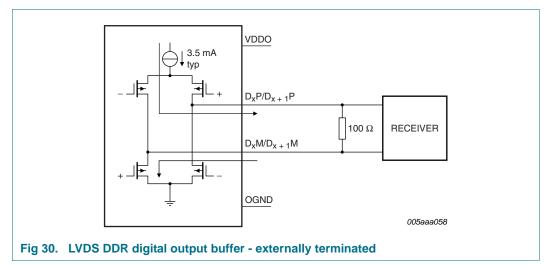


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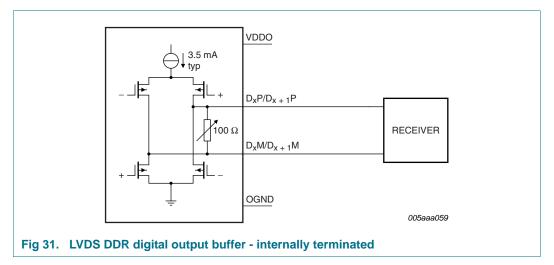
The output resistance is 50 Ω and is the combination of an internal resistor and the equivalent output resistance of the buffer. There is no need for an external damping resistor. The drive strength of both data and DAV buffers can be programmed via the SPI in order to adjust the rise and fall times of the output digital signals (see Table 30):

11.5.2 Digital output buffers: LVDS DDR mode

The digital output buffers can be configured as LVDS DDR by setting bit LVDS_CMOS to logic 1 (see Table 23).



Each output should be terminated externally with a 100 Ω resistor (typical) at the receiver side (Figure 30) or internally via SPI control bits LVDS_INT_TER[2:0] (see Figure 31 and Table 32).



The default LVDS DDR output buffer current is set to 3.5 mA. It can be programmed via the SPI (bits DAVI[1:0] and DATA[1:0]; see <u>Table 31</u>) in order to adjust the output logic voltage levels.

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Table 14.	LVDS DDR output reg	jister 2
-----------	---------------------	----------

Resistor value (Ω)
no internal termination
300
180
110
150
100
81
60

11.5.3 DAta Valid (DAV) output clock

A data valid output clock signal (DAV) can be used to capture the data delivered by the ADC1010S. Detailed timing diagrams for CMOS and LVDS DDR modes are shown in Figure 4 and Figure 5 respectively.

11.5.4 OuT-of-Range (OTR)

An out-of-range signal is provided on pin OTR. The latency of OTR is fourteen clock cycles. The OTR response can be speeded up by enabling Fast OTR (bit FASTOTR = logic 1; see <u>Table 29</u>). In this mode, the latency of OTR is reduced to only four clock cycles. The Fast OTR detection threshold (below full-scale) can be programmed via bits FASTOTR_DET[2:0].

Table	15.	Fast OTR register	

FASTOTR_DET[2:0]	Detection level (dB)
000	-20.56
001	-16.12
010	-11.02
011	-7.82
100	-5.49
101	-3.66
110	-2.14
111	-0.86

11.5.5 Digital offset

By default, the ADC1010S delivers output code that corresponds to the analog input. However it is possible to add a digital offset to the output code via the SPI (bits DIG_OFFSET[5:0]; see <u>Table 25</u>).

11.5.6 Test patterns

For test purposes, the ADC1010S can be configured to transmit one of a number of predefined test patterns (via bits TESTPAT_SEL[2:0]; see <u>Table 26</u>). A custom test pattern can be defined by the user (TESTPAT_USER[9:0]; see <u>Table 27</u> and <u>Table 28</u>) and is selected when TESTPAT_SEL[2:0] = 101. The selected test pattern is transmitted regardless of the analog input.

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11.5.7	Output	codes	versus	input	voltage
--------	--------	-------	--------	-------	---------

Table 16. Ou	Itput codes		
$V_{\text{INP}} - V_{\text{INM}}$	Offset binary	Two's complement	OTR pin
< -1	00 0000 0000	10 0000 0000	1
-1.0000000	00 0000 0000	10 0000 0000	0
-0.9980469	00 0000 0001	10 0000 0001	0
-0.9960938	00 0000 0010	10 0000 0010	0
-0.9941406	00 0000 0011	10 0000 0011	0
-0.9921875	00 0000 0100	10 0000 0100	0
			0
-0.0039063	01 1111 1110	11 1111 1110	0
-0.0019531	01 111 1111	11 1111 1111	0
0.0000000	10 0000 0000	00 0000 0000	0
+0.0019531	10 0000 0001	00 0000 0001	0
+0.0039063	10 0000 0010	00 0000 0010	0
			0
+0.9921875	11 1111 1011	01 1111 1011	0
+0.9941406	11 1111 1100	01 1111 1100	0
+0.9960938	11 1111 1101	01 1111 1101	0
+0.9980469	11 1111 1110	01 1111 1110	0
+1.0000000	11 1111 1111	01 1111 1111	0
> +1	11 1111 1111	01 1111 1111	1

11.6 Serial peripheral interface

11.6.1 Register description

The ADC1010S serial interface is a synchronous serial communications port that allows easy interfacing with many commonly-used microprocessors. It provides access to the registers that control the operation of the chip.

This interface is configured as a 3-wire type (SDIO as bidirectional pin)

Pin SCLK is the serial clock input and \overline{CS} is the chip select pin.

Each read/write operation is initiated by a LOW level on pin \overline{CS} . A minimum of three bytes is transmitted (two instruction bytes and at least one data byte). The number of data bytes is determined by the value of bits W1 and W2 (see Table 18).

Table 17. Instruction bytes for the SPI

	MSB							LSB
Bit	7	6	5	4	3	2	1	0
Description	R/W[1]	W1[2]	W0[2]	A12	A11	A10	A9	A8
	A7	A6	A5	A4	A3	A2	A1	A0

[1] Bit R/W indicates whether it is a read (logic 1) or a write (logic 0) operation.

[2] Bits W1 and W0 indicate the number of bytes to be transferred after the instruction byte (see Table 18).

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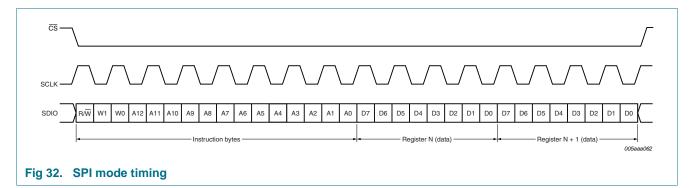
Table 18. Number of data bytes to be transferred after the instruction bytes

W1	W0	Number of bytes transmitted
0	0	1 byte
0	1	2 bytes
1	0	3 bytes
1	1	4 bytes or more

Bits A12 to A0 indicate the address of the register being accessed. In the case of a multiple byte transfer, this address is the first register to be accessed. An address counter is increased to access subsequent addresses.

The steps involved in a data transfer are as follows:

- 1. A falling edge on \overline{CS} in combination with a rising edge on SCLK determine the start of communications.
- 2. The first phase is the transfer of the 2-byte instruction.
- 3. The second phase is the transfer of the data which can vary in length but is always a multiple of 8 bits. The MSB is always sent first (for instruction and data bytes).
- 4. A rising edge on \overline{CS} indicates the end of data transmission.



11.6.2 Default modes at start-up

During circuit initialization, it does not matter which output data standard has been selected. At power-up, the device enters Pin control mode.

A falling edge on \overline{CS} triggers a transition to SPI control mode. When the ADC1010S enters SPI control mode, the output data standard (CMOS/LVDS DDR) is determined by the level on pin SDIO (see Figure 33). Once in SPI control mode, the output data standard can be changed via bit LVDS_CMOS in Table 23.

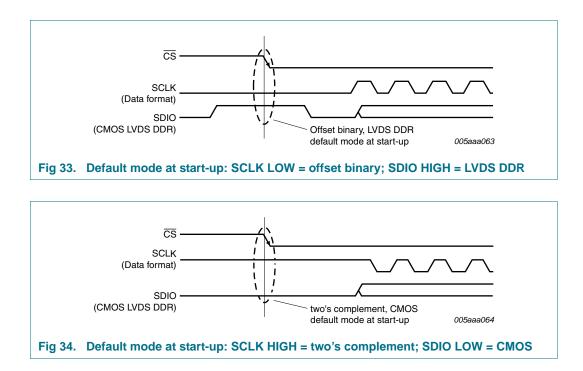
When the ADC1010S enters SPI control mode, the output data format (two's complement or offset binary) is determined by the level on pin SCLK (gray code can only be selected via the SPI). Once in SPI control mode, the output data format can be changed via bit DATA FORMAT[1:0] in Table 23.

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11.6.3 Register allocation map

Addr	Register name	R/W		Bit definition									
Hex			Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Bin		
0005	Reset and operating mode	R/W	SW_RST		RESERVED	[2:0]	-	-	OP_MC	DE[1:0]	0000 0000		
0006	Clock	R/W	-	-	-	SE_SEL	DIFF_SE	-	CLKDIV	DCS_EN	0000 0001		
0008	Internal reference	R/W	-	-	-	-	INTREF_EN		INTREF[2:0]		0000 0000		
0011	Output data standard	R/W	-	-	-	LVDS_ CMOS	OUTBUF	OUTBUS_ SWAP	DATA_FO	RMAT[1:0]	0000 0000		
0012	Output clock	R/W	-	-	-	-	DAVINV	D/	AVPHASE[2:0]		0000 1110		
0013	Offset	R/W	-	DIG_OFFSET[5:0]						0000 0000			
0014	Test pattern 1	R/W	-	TESTPAT_SEL[2:0]					0000 0000				
0015	Test pattern 2	R/W				TE	STPAT_USER[9:2]				0000 0000		
0016	Test pattern 3	R/W	TESTPA USER[1	_			-	-	-	-	0000 0000		
0017	Fast OTR	R/W	-	-	-	-	FASTOTR	FAS	TOTR_DET[2	:0]	0000 0000		
0020	CMOS output	R/W	-	-	-	-	DAV_DR\	/[1:0]	DATA_[DRV[1:0]	0000 1110		
0021	LVDS DDR O/P 1	R/W	-	-	DAVI_x2_EN		DAVI[1:0]	DATAI_ x2_EN	DATA	AI[1:0]	0000 0000		
0022	LVDS DDR O/P 2	R/W	-	-	-	-	BIT_BYTE_WISE	LVD	S_INT_TER[2	:0]	0000 0000		

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Derault	values are highlighted.			
Bit	Symbol	Access	Value	Description
7	SW_RST	R/W		reset digital section
			0	no reset
			1	performs a reset of the SPI registers
6 to 4	RESERVED[2:0]		000	reserved
3 to 2	-		00	not used
1 to 0	OP_MODE[1:0]	R/W		operating mode
			00	normal (power-up)
			01	power-down
			10	sleep
			11	normal (power-up)
-				

Table 20. Reset and operating mode control register (address 0005h) bit description Default values are highlighted. Image: Control register (address 0005h)

Table 21. Clock control register (address 0006h) bit description Default values are highlighted. Image: Clock control register (address 0006h) bit description

Bit	Symbol	Access	Value	Description
7 to 5	-		000	not used
4	SE_SEL	R/W		single-ended clock input pin select
			0	CLKM
			1	CLKP
3	DIFF_SE	R/W		differential/single ended clock input select
			0	fully differential
			1	single-ended
2	-		0	not used
1	CLKDIV	R/W		clock input divide by 2
			0	disabled
			1	enabled
0	DCS_EN	R/W		duty cycle stabilizer
			0	disabled
			1	enabled

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Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	INTREF_EN	R/W		programmable internal reference enable
			0	disable
			1	active
2 to 0	INTREF[2:0]	R/W		programmable internal reference
			000	FS = 2 V
			001	FS = 1.78 V
			010	FS = 1.59 V
			011	FS = 1.42 V
			100	FS = 1.26 V
			101	FS = 1.12 V
			110	FS = 1 V
			111	reserved

Table 22. Internal reference control register (address 0008h) bit description Default values are highlighted

 Table 23.
 Output data standard control register (address 0011h) bit description

 Default values are highlighted.
 Image: Control register (address 0011h)

Bit	Symbol	Access	Value	Description
7 to 5	-		000	not used
4	LVDS_CMOS	R/W		output data standard: LVDS DDR or CMOS
			0	CMOS
			1	LVDS DDR
3	3 OUTBUF	R/W		output buffers enable
			0	output enabled
			1	output disabled (high-Z)
2	OUTBUS_SWAP	S_SWAP R/W		output bus swapping
			0	no swapping
			1	output bus is swapping (MSB becomes LSB and vice versa)
1 to 0	DATA_FORMAT[1:0]	R/W		output data format
			00	offset binary
			01	two's complement
			10	gray code
			11	offset binary

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	values are highlighted.			
Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	DAVINV	R/W		output clock data valid (DAV) polarity
			0	normal
			1	inverted
2 to 0 D	DAVPHASE[2:0]	R/W		DAV phase select
			000	output clock shifted (ahead) by 6/16 \times t_{clk}
			001	output clock shifted (ahead) by 5/16 \times t_{clk}
			010	output clock shifted (ahead) by $4/16 \times t_{clk}$
			011	output clock shifted (ahead) by 3/16 \times t_{clk}
			100	output clock shifted (ahead) by $2/16 \times t_{clk}$
			101	output clock shifted (ahead) by $1/16 \times t_{clk}$
			110	default value as defined in timing section
			111	output clock shifted (delayed) by $1/16 \times t_{clk}$

Table 24. Output clock register (address 0012h) bit description Default values are bigblighted Image: State of the state

Table 25.Offset register (address 0013h) bit descriptionDefault values are highlighted.

	0 0			
Bit	Symbol	Access	Value	Description
7 to 6	-		00	not used
5 to 0	DIG_OFFSET[5:0]	R/W		digital offset adjustment
			011111	+31 LSB
			000000	0
			100000	-32 LSB

Table 26.Test pattern register 1 (address 0014h) bit descriptionDefault values are highlighted.

		-		
Bit	Symbol	Access	Value	Description
7 to 3	-		00000	not used
2 to 0 TES	TESTPAT_SEL[2:0]	R/W		digital test pattern select
			000	off
			001	mid scale
			010	-FS
			011	+FS
			100	toggle '11111111'/'00000000'
			101	custom test pattern
			110	'10101010.'
			111	'0101010'

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Table 27. Test pattern register 2 (address 0015h) bit description

Default values are highlighted.

	alaee ale nighteat			
Bit	Symbol	Access	Value	Description
7 to 0	TESTPAT_USER[9:2]	R/W	0000000	custom digital test pattern (bits 9 to 2)

Table 28. Test pattern register 3 (address 0016h) bit description

Default values are highlighted.

Bit	Symbol	Access	Value	Description
7 to 6	TESTPAT_USER[1:0]	R/W	00	custom digital test pattern (bits 1 to 0)
5 to 0	-		000000	not used

Table 29. Fast OTR register (address 0017h) bit description

Default values are highlighted.

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	FASTOTR R/W fast Ou		fast OuT-of-Range (OTR) detection	
			0	disabled
			1	enabled
2 to 0	FASTOTR_DET[2:0]	R/W		set fast OTR detect level
			000	–20.56 dB
			001	–16.12 dB
			010	–11.02 dB
			011	-7.82 dB
			100	–5.49 dB
			101	–3.66 dB
			110	–2.14 dB
			111	–0.86 dB

Table 30. CMOS output register (address 0020h) bit description Default values are highlighted. Image: Comparison of the second second

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3 to 2	DAV_DRV[1:0]	:0] R/W drive strength for DAV CI		drive strength for DAV CMOS output buffer
			00	low
			01	medium
			10	high
			11	very high
1 to 0	DATA_DRV[1:0]	R/W		drive strength for DATA CMOS output buffer
			00	low
			01	medium
			10	high
			11	very high

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Bit	Symbol	Access	Value	Description
7 to 6	-		00	not used
5	DAVI_x2_EN	R/W		double LVDS current for DAV LVDS buffer
			0	disabled
			1	enabled
4 to 3	DAVI[1:0]	R/W		LVDS current for DAV LVDS buffer
			00	3.5 mA
			01	4.5 mA
			10	1.25 mA
			11	2.5 mA
2	DATAI_x2_EN	R/W		double LVDS current for DATA LVDS buffer
			0	disabled
			1	enabled
1 to 0	DATAI[1:0]	R/W		LVDS current for DATA LVDS buffer
			00	3.5 mA
			01	4.5 mA
			10	1.25 mA
			11	2.5 mA

Table 31. LVDS DDR output register 1 (address 0021h) bit description Default values are highlighted.

Table 32. LVDS DDR output register 2 (address 0022h) bit description Default values are highlighted.

Bit	Symbol	Access	Value	Description
7 to 4	-		0000	not used
3	BIT_BYTE_WISE	R/W		DDR mode for LVDS output
			0	bit wise (even data bits output on DAV rising edge/odd data bits output on DAV falling edge)
			1	byte wise (MSB data bits output on DAV rising edge/LSB data bits output on DAV falling edge)
2 to 0	LVDS_INT_TER[2:0]	R/W		internal termination for LVDS buffer (DAV and DATA)
			000	no internal termination
			001	300 Ω
			010	180 Ω
			011	110 Ω
			100	150 Ω
			101	100 Ω
			110	81 Ω
			111	60 Ω

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12. Package outline

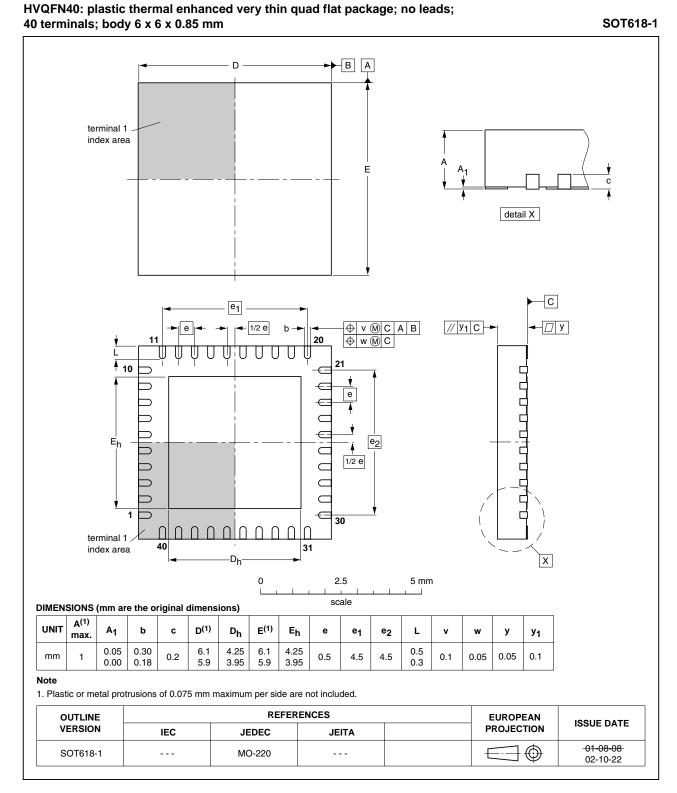


Fig 35. Package outline SOT618-1 (HVQFN40)

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13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ADC1010S_SER v.2	20101228	Product data sheet	-	ADC1010S_SER_1
Modifications:	 Text and dra SOT618-6 c Figure 35 "P 	status changed from Prelimi wings updated throughout of hanged to SOT618-1. See Package outline SOT618-1 ("Typical characteristics" ac	entire data she Table 1 "Orderi HVQFN40)".	et. <u>ng information"</u> and
DC1010S_SER_1	20100409	Preliminary data sheet	-	-

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14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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